

## Silicon PIN Photodiode



### FEATURES

- Package type: surface mount
- Package form: GW, RGW
- Dimensions (L x W x H in mm): 6.4 x 3.9 x 1.2
- Radiant sensitive area (in mm<sup>2</sup>): 4.4
- High photo sensitivity
- High radiant sensitivity
- Suitable for visible and near infrared radiation
- Fast response times
- Angle of half sensitivity:  $\varphi = \pm 65^\circ$
- Floor life: 168 h, MSL 3, acc. J-STD-020
- Lead (Pb)-free reflow soldering
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC


**RoHS**  
COMPLIANT

### DESCRIPTION

VBP104S and VBP104SR are high speed and high sensitive PIN photodiodes. It is a surface mount device (SMD) including the chip with a 4.4 mm<sup>2</sup> sensitive area detecting visible and near infrared radiation.

### APPLICATIONS

- High speed photo detector

### PRODUCT SUMMARY

COMPONENT	$I_{ra}$ ( $\mu A$ )	$\varphi$ (deg)	$\lambda_{0.1}$ (nm)
VBP104S	35	$\pm 65$	430 to 1100
VBP104SR	35	$\pm 65$	430 to 1100

#### Note

- Test conditions see table "Basic Characteristics"

### ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
VBP104S	Tape and reel	MOQ: 1000 pcs, 1000 pcs/reel	Gullwing
VBP104SR	Tape and reel	MOQ: 1000 pcs, 1000 pcs/reel	Reverse gullwing

#### Note

- MOQ: minimum order quantity

### ABSOLUTE MAXIMUM RATINGS ( $T_{amb} = 25^\circ C$ , unless otherwise specified)

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		$V_R$	60	V
Power dissipation	$T_{amb} \leq 25^\circ C$	$P_V$	215	mW
Junction temperature		$T_j$	100	$^\circ C$
Operating temperature range		$T_{amb}$	- 40 to + 100	$^\circ C$
Storage temperature range		$T_{stg}$	- 40 to + 100	$^\circ C$
Soldering temperature	Acc. reflow solder profile fig. 8	$T_{sd}$	260	$^\circ C$
Thermal resistance junction/ambient		$R_{thJA}$	350	K/W

BASIC CHARACTERISTICS ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 50\text{ mA}$	$V_F$		1	1.3	V
Breakdown voltage	$I_R = 100\text{ }\mu\text{A}$ , $E = 0$	$V_{(BR)}$	60			V
Reverse dark current	$V_R = 10\text{ V}$ , $E = 0$	$I_{ro}$		2	30	nA
Diode capacitance	$V_R = 0\text{ V}$ , $f = 1\text{ MHz}$ , $E = 0$	$C_D$		48		pF
	$V_R = 3\text{ V}$ , $f = 1\text{ MHz}$ , $E = 0$	$C_D$		17	40	pF
Open circuit voltage	$E_e = 1\text{ mW/cm}^2$ , $\lambda = 950\text{ nm}$	$V_o$		350		mV
Temperature coefficient of $V_o$	$E_e = 1\text{ mW/cm}^2$ , $\lambda = 950\text{ nm}$	$TK_{V_o}$		-2.6		mV/K
Short circuit current	$E_e = 1\text{ mW/cm}^2$ , $\lambda = 950\text{ nm}$	$I_k$		32		$\mu\text{A}$
Temperature coefficient of $I_k$	$E_e = 1\text{ mW/cm}^2$ , $\lambda = 950\text{ nm}$	$TK_{I_k}$		0.1		%/K
Reverse light current	$E_e = 1\text{ mW/cm}^2$ , $\lambda = 950\text{ nm}$ , $V_R = 5\text{ V}$	$I_{ra}$	25	35		$\mu\text{A}$
Angle of half sensitivity		$\phi$		$\pm 65$		deg
Wavelength of peak sensitivity		$\lambda_p$		940		nm
Range of spectral bandwidth		$\lambda_{0.1}$		430 to 1100		nm
Noise equivalent power	$V_R = 10\text{ V}$ , $\lambda = 950\text{ nm}$	NEP		$4 \times 10^{-14}$		$\text{W}/\sqrt{\text{Hz}}$
Rise time	$V_R = 10\text{ V}$ , $R_L = 1\text{ k}\Omega$ , $\lambda = 820\text{ nm}$	$t_r$		100		ns
Fall time	$V_R = 10\text{ V}$ , $R_L = 1\text{ k}\Omega$ , $\lambda = 820\text{ nm}$	$t_f$		100		ns

## BASIC CHARACTERISTICS ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)

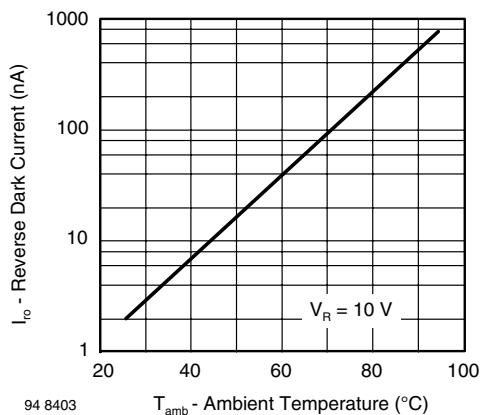


Fig. 1 - Reverse Dark Current vs. Ambient Temperature

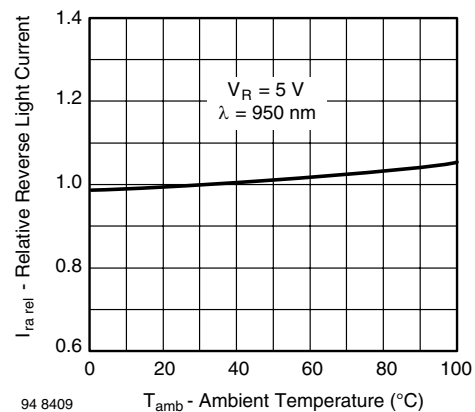


Fig. 2 - Relative Reverse Light Current vs. Ambient Temperature

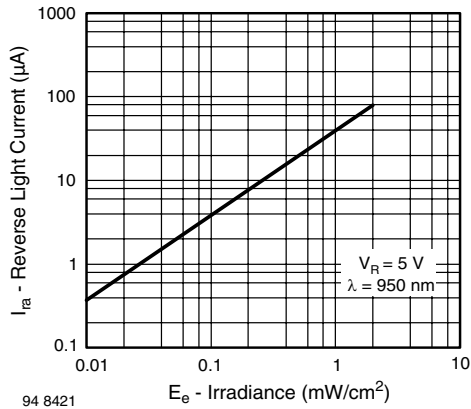


Fig. 3 - Reverse Light Current vs. Irradiance

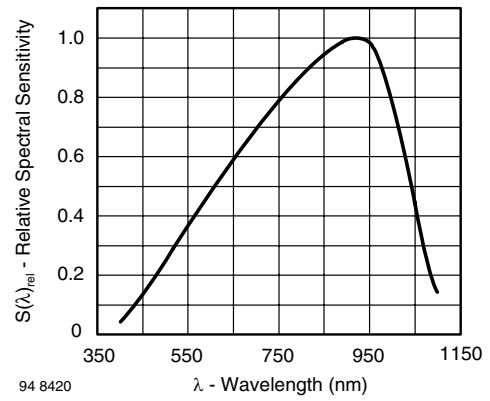


Fig. 6 - Relative Spectral Sensitivity vs. Wavelength

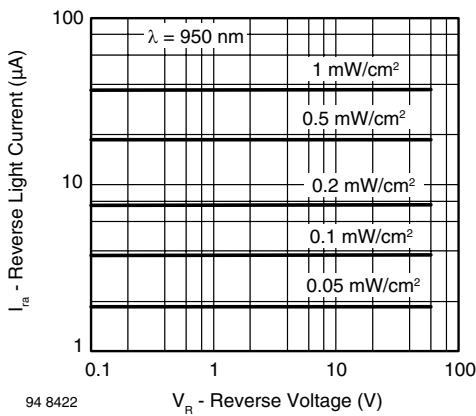


Fig. 4 - Reverse Light Current vs. Reverse Voltage

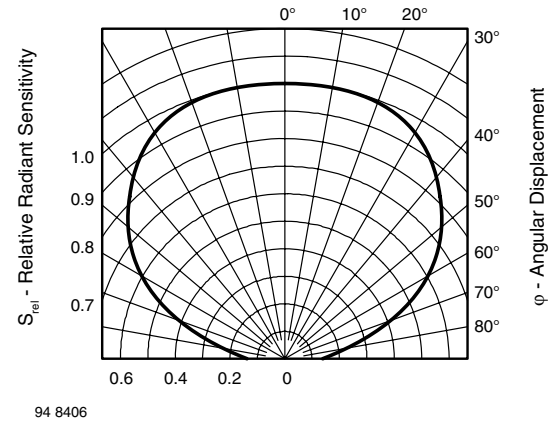


Fig. 7 - Relative Radiant Sensitivity vs. Angular Displacement

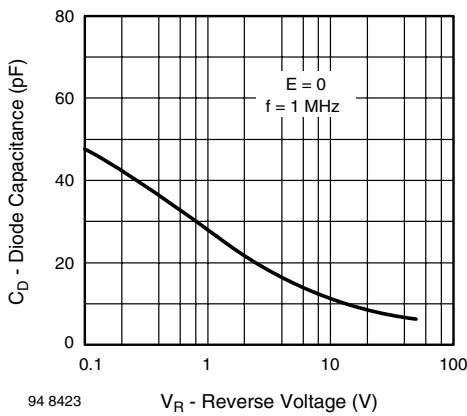


Fig. 5 - Diode Capacitance vs. Reverse Voltage

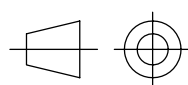
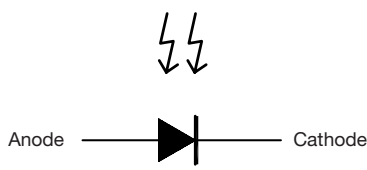
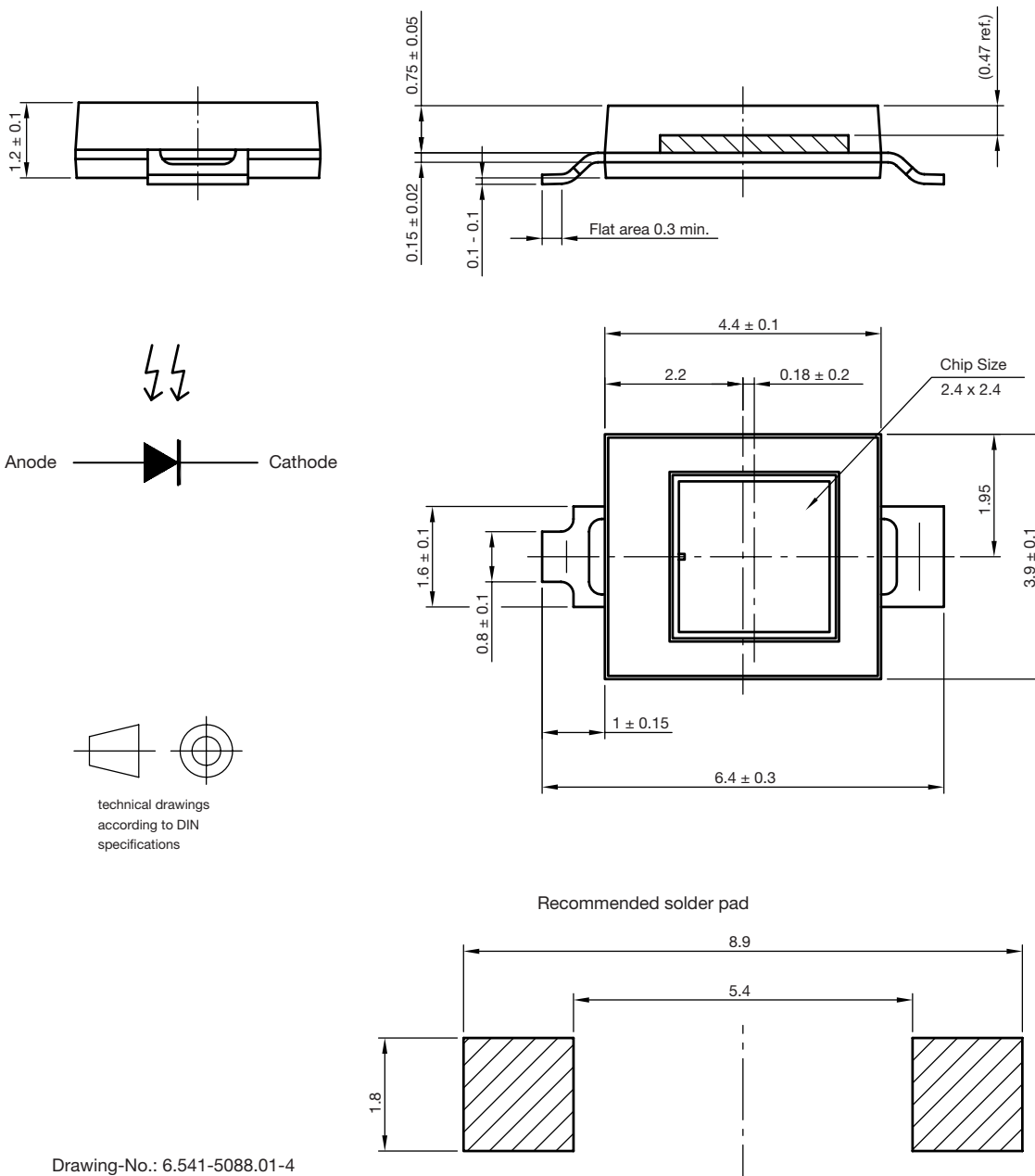
# VBP104S, VBP104SR

Vishay Semiconductors

Silicon PIN Photodiode



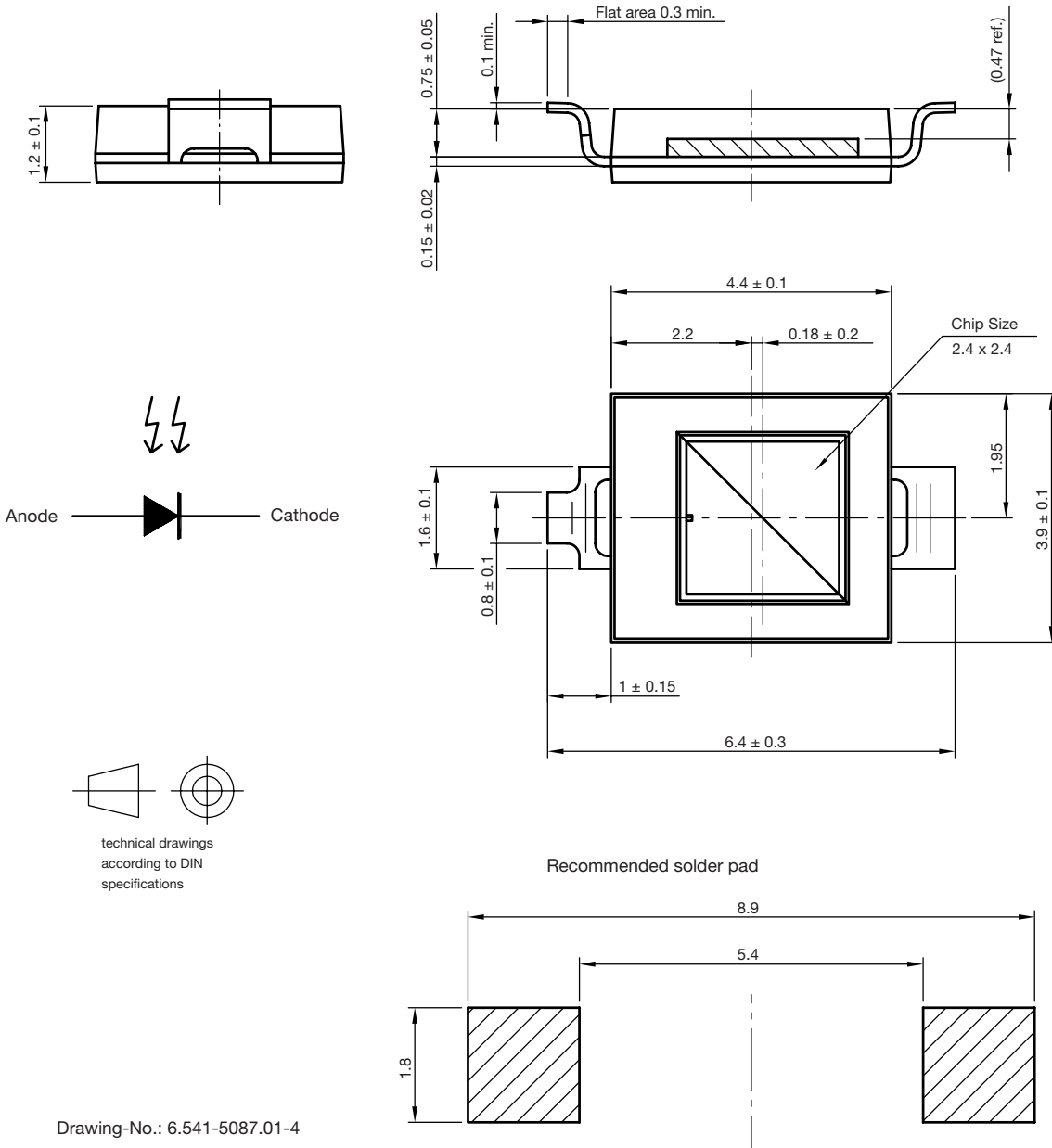
## PACKAGE DIMENSIONS FOR VBP104S in millimeters



technical drawings according to DIN specifications

Drawing-No.: 6.541-5088.01-4  
Issue: 1; 15.04.10  
22107

**PACKAGE DIMENSIONS FOR VBP104SR** in millimeters



Drawing-No.: 6.541-5087.01-4  
 Issue: 1; 15.04.10  
 22106

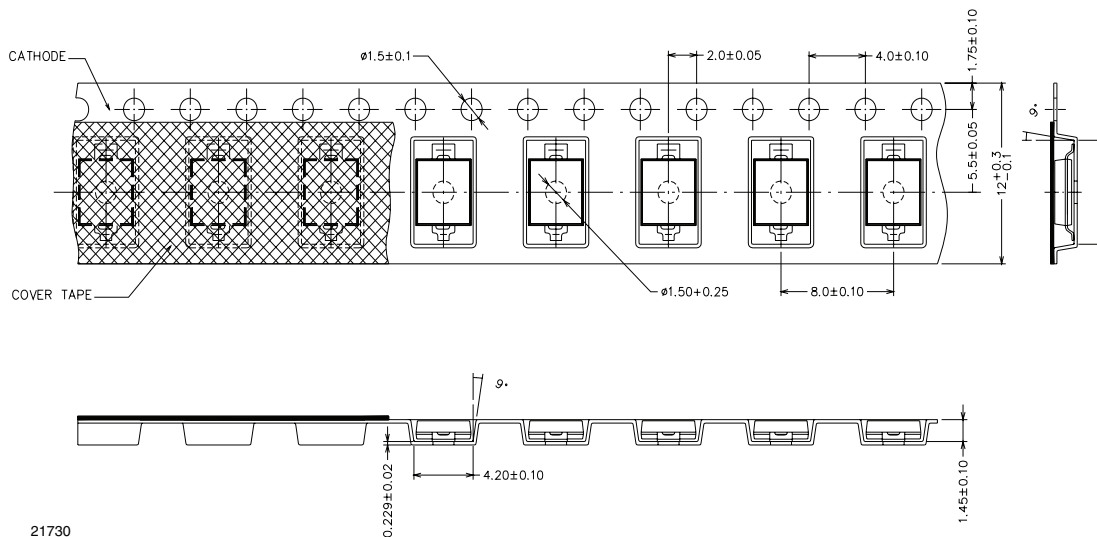
# VBP104S, VBP104SR

Vishay Semiconductors

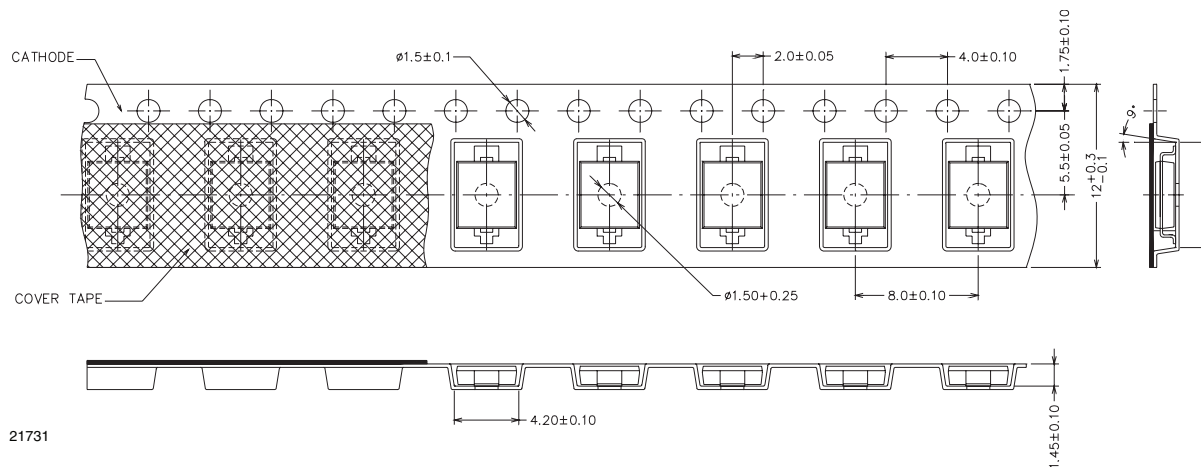
Silicon PIN Photodiode



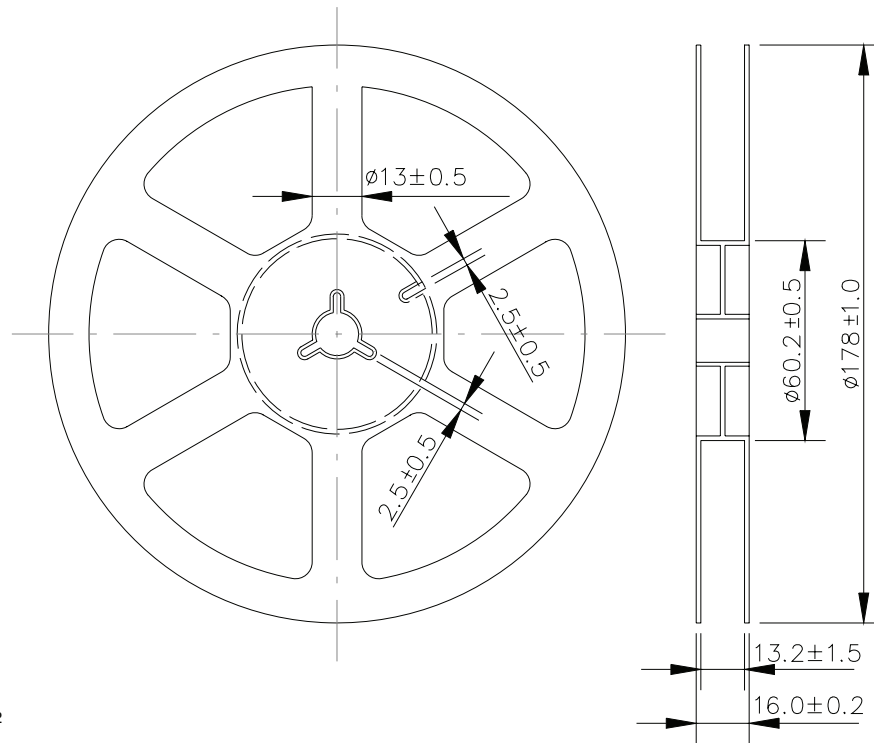
## TAPING DIMENSIONS FOR VBP104S in millimeters



## TAPING DIMENSIONS FOR VBP104SR in millimeters

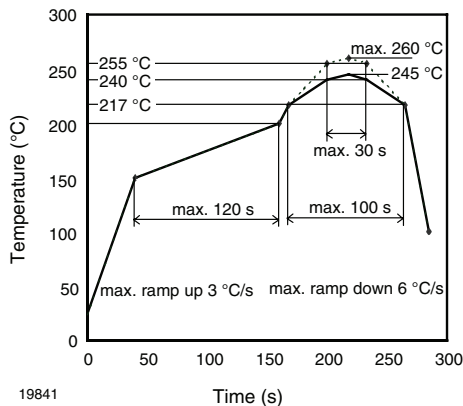


**REEL DIMENSIONS FOR VBP104S AND VBP104SR** in millimeters



21732

**SOLDER PROFILE**



19841

Fig. 8 - Lead (Pb)-free Reflow Solder Profile acc. J-STD-020

**DRYPACK**

Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

**FLOOR LIFE**

Time between soldering and removing from MBB must not exceed the time indicated in J-STD-020:  
 Moisture sensitivity: level 3  
 Floor life: 168 h  
 Conditions:  $T_{amb} < 30\text{ }^{\circ}\text{C}$ ,  $RH < 60\%$

**DRYING**

In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-020 or recommended conditions:  
 192 h at  $40\text{ }^{\circ}\text{C}$  (+ 5 °C),  $RH < 5\%$   
 or  
 96 h at  $60\text{ }^{\circ}\text{C}$  (+ 5 °C),  $RH < 5\%$ .



## Disclaimer

All product specifications and data are subject to change without notice.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained herein or in any other disclosure relating to any product.

Vishay disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless otherwise expressly indicated. Customers using or selling Vishay products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Vishay for any damages arising or resulting from such use or sale. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

Product names and markings noted herein may be trademarks of their respective owners.